Product Specification

PE95420

Radiation Tolerant UltraCMOS® SPDT RF Switch Hermetically Sealed Ceramic Package, 1–8500 MHz

Product Description

The PE95420 is an RF SPDT switch available in a hermetically sealed ceramic package and also available in die. The PE95420 is designed to cover a broad range of applications from 1 to 8500 MHz for use in various High-Reliability (Hi-Rel) industries and applications requiring broadband performance. It uses Peregrine's UltraCMOS® process and features HaRP™ technology enhancements to deliver high linearity and exceptional harmonics performance. HaRP technology is an innovative feature of the UltraCMOS process providing upgraded linearity performance.

The PE95420 is an absorptive/non-reflective switch design, which is an ideal termination method for RF elements in a system design. A single-pin 3.3V CMOS logic control in a single chip solution reduces the number of control lines.

Typical Industries

- Medical
- Automotive
- Telecom infrastructure
- Test instrumentation
- Down-hole oil/gas
- Military
- Commercial space applications

Features

- HaRP™ technology enhanced
  - Eliminates gate and phase lag
  - No insertion loss or phase drift
- High linearity: 60 dBm IIP3
- Low insertion loss
  - 0.77 dB @ 100 MHz
  - 1.00 dB @ 3000 MHz
  - 1.15 dB @ 6000 MHz
  - 1.38 dB @ 8500 MHz
- High isolation (RF1–RF2)
  - 86.5 dB @ 100 MHz
  - 48.2 dB @ 3000 MHz
  - 36.6 dB @ 6000 MHz
  - 27.8 dB @ 8500 MHz
- Fast switching time
  - 700 ns RF ON
  - 300 ns RF OFF
- Low power consumption: 3.3 µW @ 3.3V
- 1 dB compression point of +33 dBm
- Single-pin 3.3V CMOS logic control
- ESD tolerant to 2000V HBM
- Absorptive/non-reflective
- Offered in a 7-lead hermetic CQFP surface-mount package and in DIE form

Figure 1. Functional Diagram

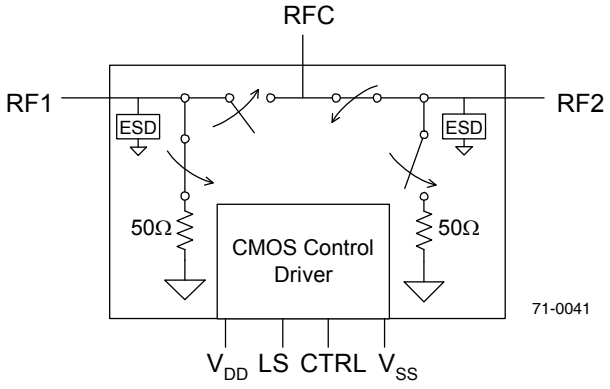


Figure 2. Package Type
7-lead CQFP

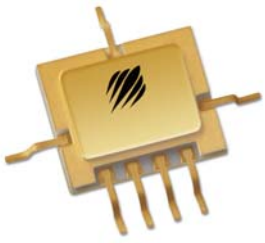


Table 1. Electrical Specifications @ –40 °C ≤ T ≤ +85 °C, 3.0V ≤ V_{DD} ≤ 3.6V

Parameter	Condition	Min	Typ	Max	Unit
Operational frequency		1		8500	MHz
Insertion loss	100 MHz		0.77	0.95	dB
	3000 MHz		1	1.28	dB
	6000 MHz		1.15	1.42	dB
	8500 MHz		1.38	1.72	dB
Isolation – RFC to RF1	100 MHz	74	75.6		dB
	3000 MHz	46	47.4		dB
	6000 MHz	43.8	48		dB
	8500 MHz[2]	31	38		dB
Isolation – RFC to RF2	100 MHz	73.7	75.4		dB
	3000 MHz	46.8	48.3		dB
	6000 MHz	45	52.1		dB
	8500 MHz[2]	31	38		dB
Isolation – RF1 to RF2	100 MHz		86.5		dB
	3000 MHz		48.2		dB
	6000 MHz		36.6		dB
	8500 MHz		27.8		dB
Return loss active port – ON state	100 MHz		21		dB
	3000 MHz		33		dB
	6000 MHz		20		dB
	8500 MHz		15		dB
Return loss active port – OFF state	100 MHz		20		dB
	3000 MHz		18		dB
	6000 MHz		15		dB
	8500 MHz		8		dB
Input 1 dB compression[1]	8500 MHz		33		dBm
Input IP3	8500 MHz, 18 dBm input power/tone		60		dBm
Switching time	50% CTRL to 90% of final value when RF ON		700		ns
	50% CTRL to 10% of final value when RF OFF		300		ns

Notes: 1. Please note maximum operating P_{IN} (50Ω) of +24 dBm in *Table 4*.
2. Guaranteed but not tested.

Figure 3. Pin Layout (Top View)

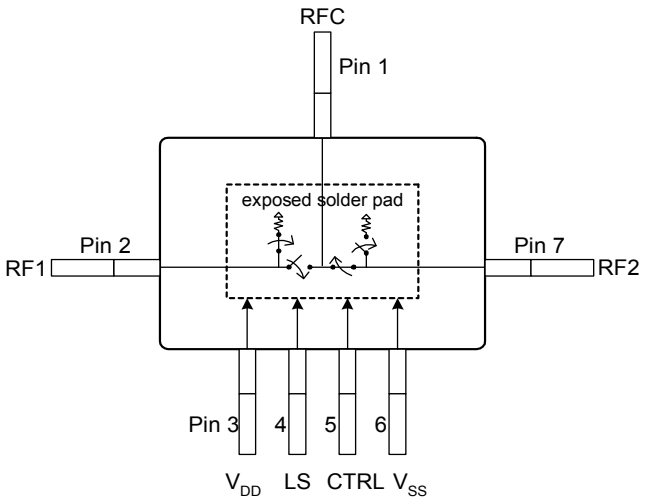


Table 2. Pin Descriptions

Pin #	Pin Name	Description
1	RFC[1]	RF common
2	RF1[1]	RF port
3	V_{DD}	Supply voltage (nominal 3.3V)
4	LS	Selects the RF1 to RFC path (See *Table 6*)
5	CTRL	Selects the RF2 to RFC path (See *Table 6*)
6	V_{SS}	Negative power supply. Apply nominal –3.3V supply
7	RF2[1]	RF port
Pad	GND[2]	Exposed pad: Grounded for proper operation

Notes: 1. All RF pins must be DC blocked with an external series capacitor or held at 0 VDC.
2. Must be soldered to PCB RF ground for proper operation.

Table 3. Operating Ranges

Symbol	Parameter	Min	Typ	Max	Unit
V_{DD}	Positive supply voltage	3.0	3.3	3.6	V
V_{SS}	Negative supply voltage	–3.6	–3.3	–3.0	V
I_{DD}	Supply current (V_{DD} = 3.3V, LS or CTRL = 3.3V)		<1		µA
I_{SS}	Supply current (V_{SS} = –3.3V)		<1		µA
	Control voltage high	$0.7\times V_{DD}$			V
	Control voltage low			$0.3\times V_{DD}$	V
T_{OP}	Operating temperature range	–40		+85	°C
P_{IN}	RF power in (50Ω) 1 MHz ≤ 8.5 GHz			24	dBm

Table 4. Absolute Maximum Ratings

Symbol	Parameter/Condition	Min	Max	Unit
V_{DD}	Power supply voltage	–0.3	4.0	V
V_{SS}	Negative supply voltage	–4.0	0.3	V
V_{C1}	Voltage on LS input	–0.3	V_{DD} + 0.3	V
V_{C2}	Voltage on CTRL input	–0.3	V_{DD} + 0.3	V
P_{IN}	RF power in (50Ω) 1 MHz ≤ 8.5 GHz		27	dBm
Θ_{JC}	Theta JC		24	°C/W
T_{ST}	Storage temperature range	–65	+150	°C
V_{ESD}	ESD voltage HBM*, all pins		2000	V

Note: * Human Body Model (MIL-STD-883 Method 3015).

Exceeding absolute maximum ratings may cause permanent damage. Operation should be restricted to the limits in the Operating Ranges table. Operation between operating range maximum and absolute maximum for extended periods may reduce reliability.

Electrostatic Discharge (ESD) Precautions

When handling this UltraCMOS device, observe the same precautions that you would use with other ESD-sensitive devices. Although this device contains circuitry to protect it from damage due to ESD, precautions should be taken to avoid exceeding the rate specified.

Latch-Up Immunity

Unlike conventional CMOS devices, UltraCMOS devices are immune to latch-up.

Table 5. Truth Table

LS	CTRL	RFC–RF1	RFC–RF2	Logic State
0	0	off	off	OFF state
0	1	off	on	RF2 active
1	0	on	off	RF1 active
1	1	N/A*	N/A*	N/A*

Note: * Invalid state that should not be used for normal operation.

Table 6. Post Radiation Table

Total Dose	Parameter/Condition	Min	Max	Unit
Post* 20 kRad	I_{DD} Positive supply current		100	µA
	I_{SS} Negative supply current	–500		µA
Post 100 kRad	I_{DD} Positive supply current		0.5	mA
	I_{SS} Negative supply current	–5		mA

Note: * Characterized but not tested.

Table 7. Single Event Effects

SEE Mode	Effective linear energy transfer (LET)
SEL/SEB/SEGR	90 MeV•mg/cm^2
SEFI	90 MeV•mg/cm^2
SEU	90 MeV•mg/cm^2
SET	90 MeV•mg/cm^2

SEL, SEB, SEGR, SEFI, SEU: None observed, Au/60 degrees.
SET: No events exceeding ±10 mV transient observed.

ELDRS

UltraCMOS devices do not include bipolar minority carrier elements and; therefore, do not exhibit enhanced low-dose-rate sensitivity.

Typical Performance Data

Figure 4. Insertion Loss: RF1 @ V_{DD} = –V_{SS} = 3.3V

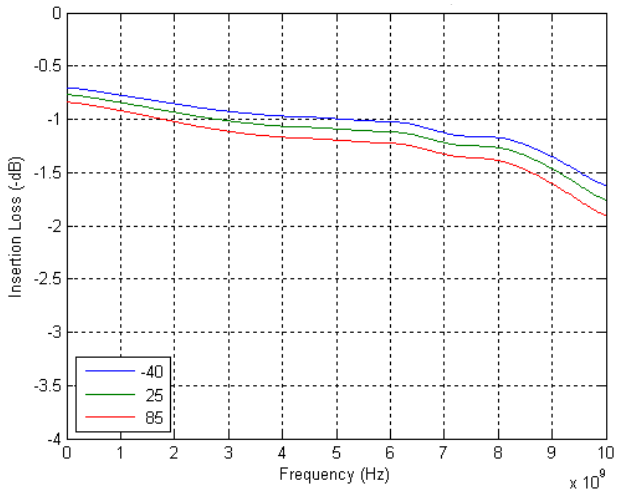


Figure 5. Insertion Loss: RF1 @ 25 °C

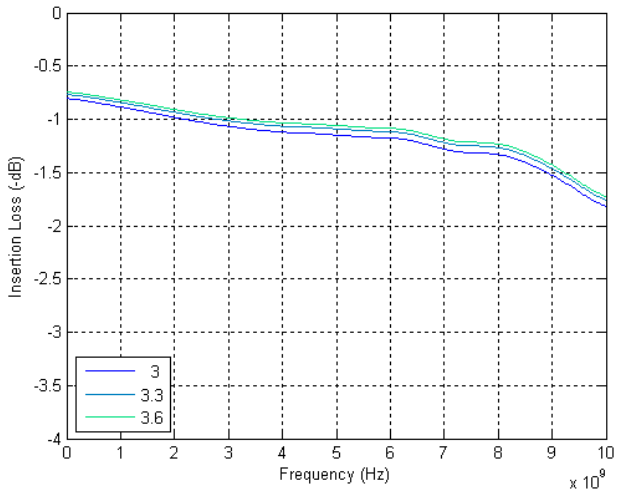


Figure 6. Insertion Loss: RF2 @ V_{DD} = –V_{SS} = 3.3V

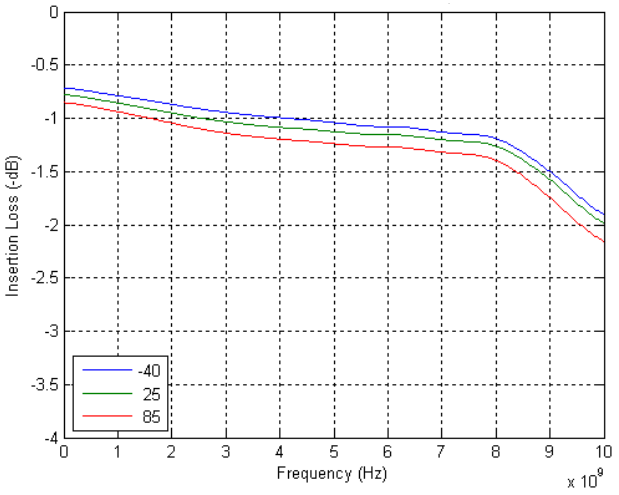
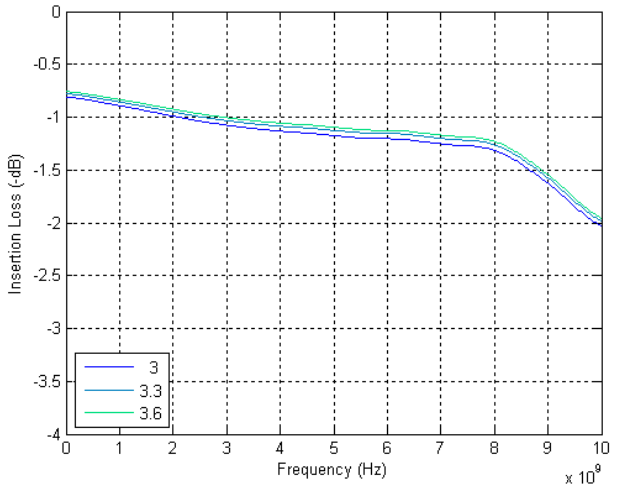


Figure 7. Insertion Loss: RF2 @ 25 °C



Typical Performance Data (Cont.)

Figure 8. Isolation: RF1–RF2, RF1 Active @ V_{DD} = –V_{SS} = 3.3V

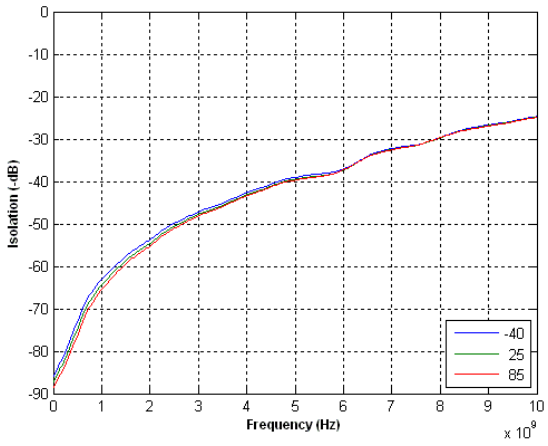


Figure 9. Isolation: RF2–RF1, RF2 Active @ V_{DD} = –V_{SS} = 3.3V

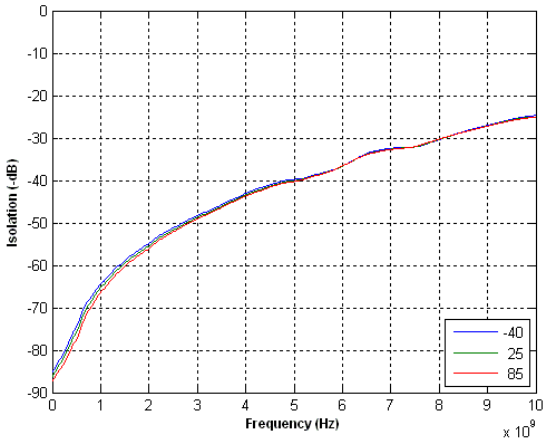


Figure 10. Isolation: RF1–RF2, RF1 Active @ 25 °C

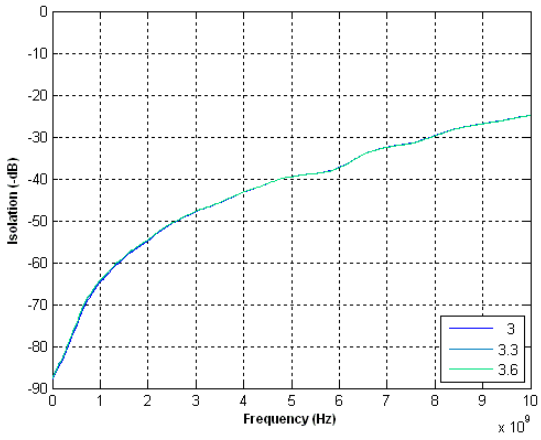


Figure 11. Isolation: RF2–RF1, RF2 Active @ 25 °C

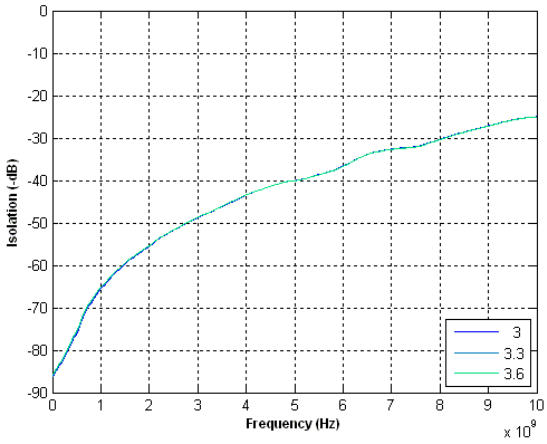


Figure 12. Isolation: RFC–RF1, RF2 Active @ V_{DD} = –V_{SS} = 3.3V

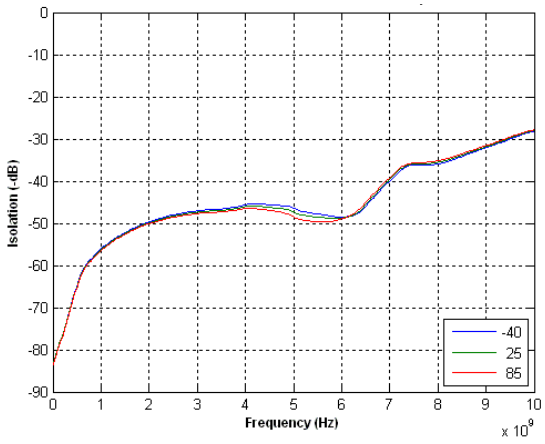
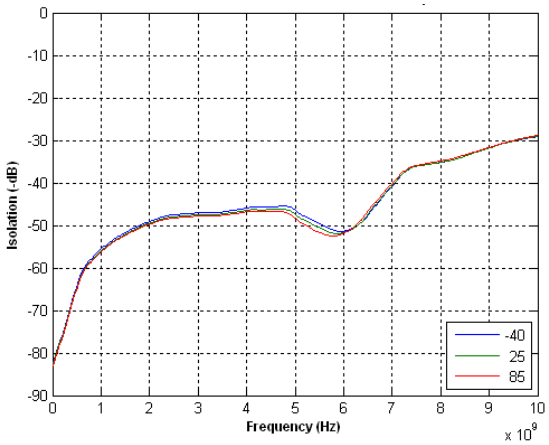


Figure 13. Isolation: RFC–RF2, RF1 Active @ V_{DD} = –V_{SS} = 3.3V



Typical Performance Data (Cont.)

Figure 14. Isolation: RFC–RF1, RF2 Active @ 25 °C

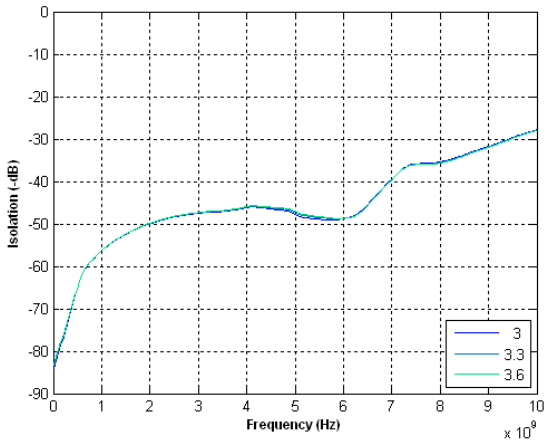


Figure 15. Isolation: RFC–RF2, RF1 Active @ 25 °C

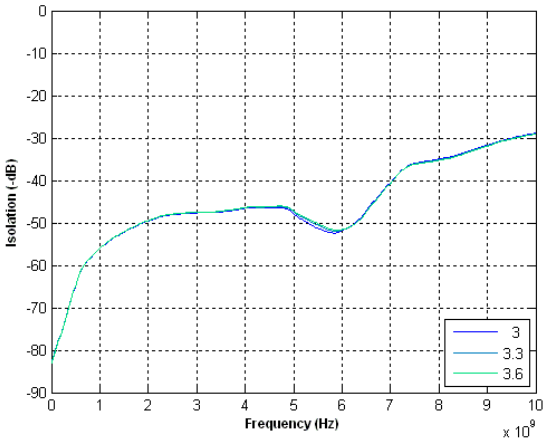


Figure 16. Isolation: RFC–RF1, OFF State @ V_{DD} = –V_{SS} = 3.3V

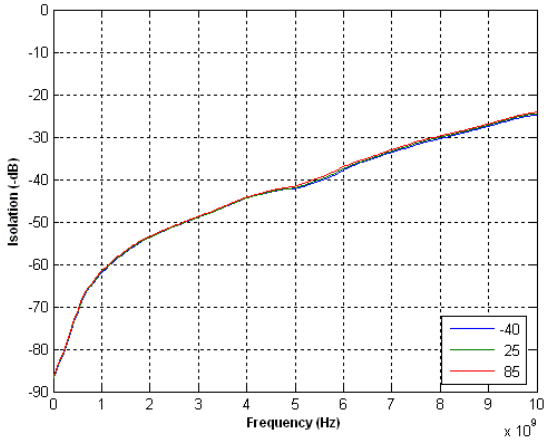


Figure 17. Isolation: RFC-RF2, OFF State @ V_DV_{DD} = –V_{SS} = 3.3V

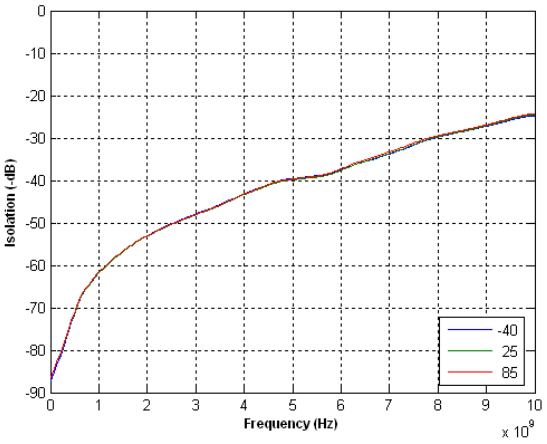


Figure 18. Isolation: RFC–RF1, OFF State @ 25 °C

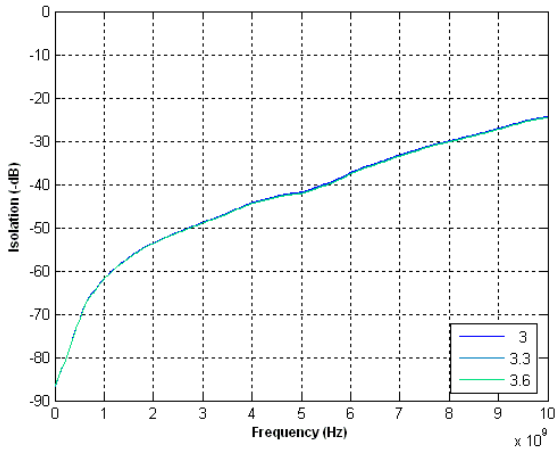
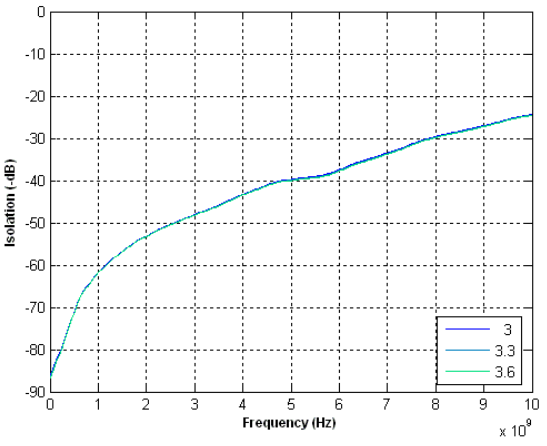


Figure 19. Isolation: RFC–RF2, OFF State @ 25 °C



Typical Performance Data (Cont.)

Figure 20. Return Loss: RF1 @ V_{DD} = –V_{SS} = 3.3V

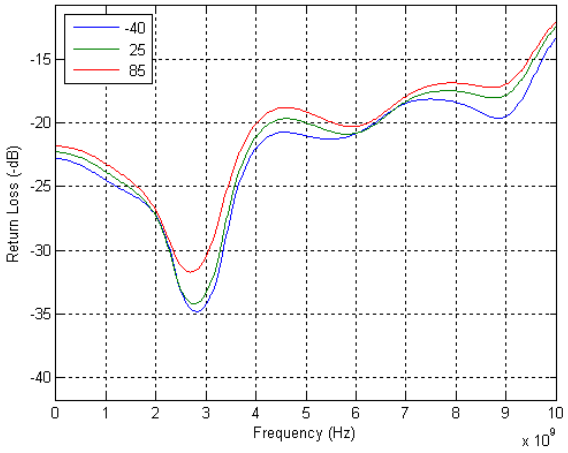


Figure 21. Return Loss: RF2 @ V_{DD} = –V_{SS} = 3.3V

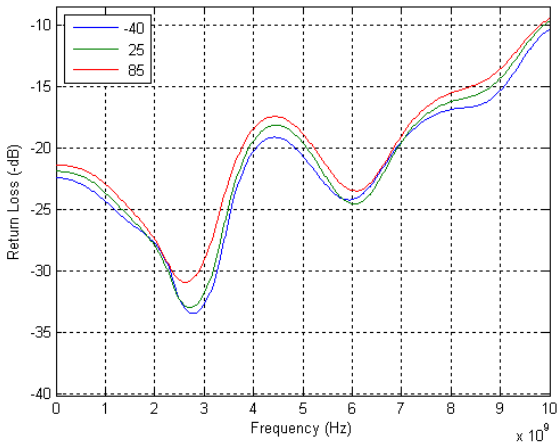


Figure 22. Return Loss: RF1 @ 25 °C

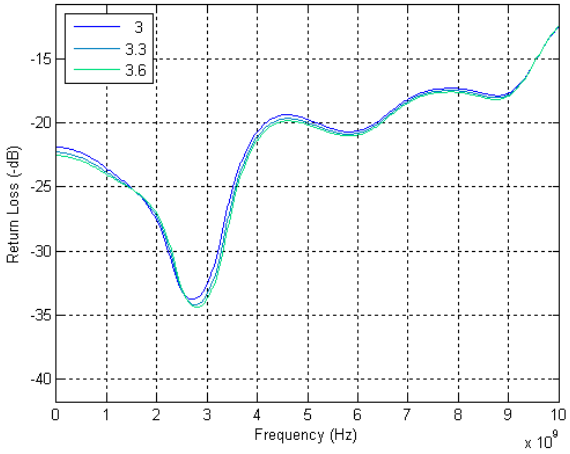
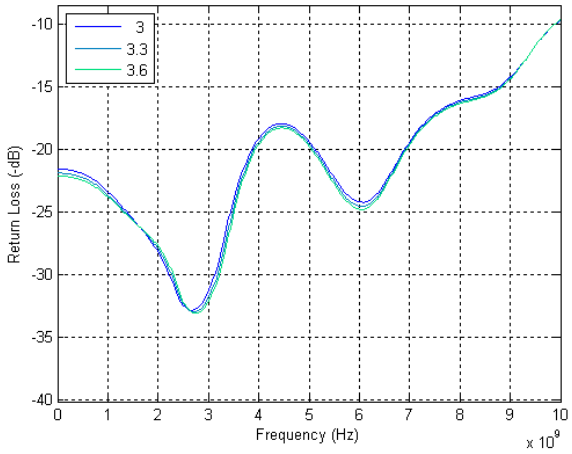


Figure 23. Return Loss: RF2 @ 25 °C

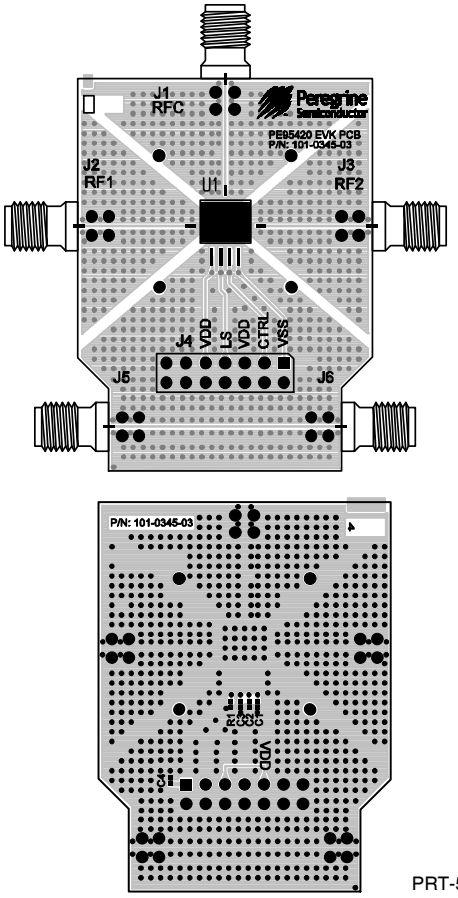


Evaluation Board

The SPDT switch evaluation board was designed to ease customer evaluation of Peregrine's PE95420. The RF common port is connected through a 50Ω transmission line via the top SMA connector, J1. RF1 and RF2 are connected through 50Ω transmission lines via SMA connectors J2 and J3, respectively. A through 50Ω transmission is available via SMA connectors J5 and J6. This transmission line can be used to estimate the loss of the PCB over the environmental conditions being evaluated.

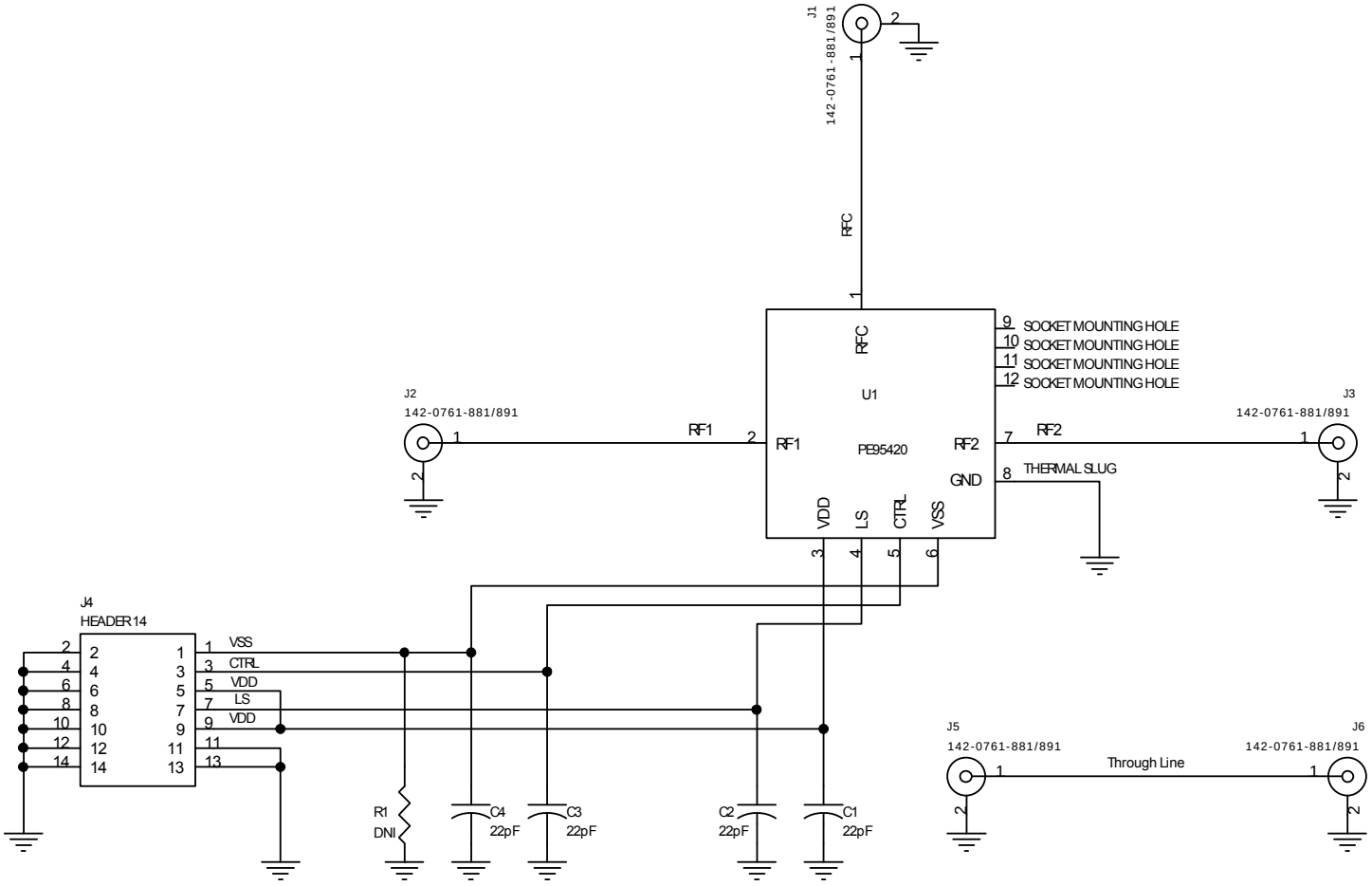
The evaluation kit board is constructed of four metal layers. The dual clad top RF layer is Rogers RO4003 material with an 8 mil RF core and ε_r = 3.55. The other two dielectric layers are FR4 for DC control and overall board strength with a cumulative board thickness of 62 mils. The RF transmission lines were designed using a grounded co-planar waveguide with a linewidth of 15 mils and gap of 7 mils.

Figure 24. Evaluation Board Layout



PRT-51554

Figure 25. Evaluation Kit Schematic



Notes: 1. Use PRT-51554 PCB.
2. Caution: Contains parts and assemblies susceptible to damage by electrostatic discharge (ESD).
3. All transmission lines are 15 mil width, 7 mil gaps, 8 mil core dielectric.

DOC-28927

Figure 26. Package Drawing
7-lead CQFP

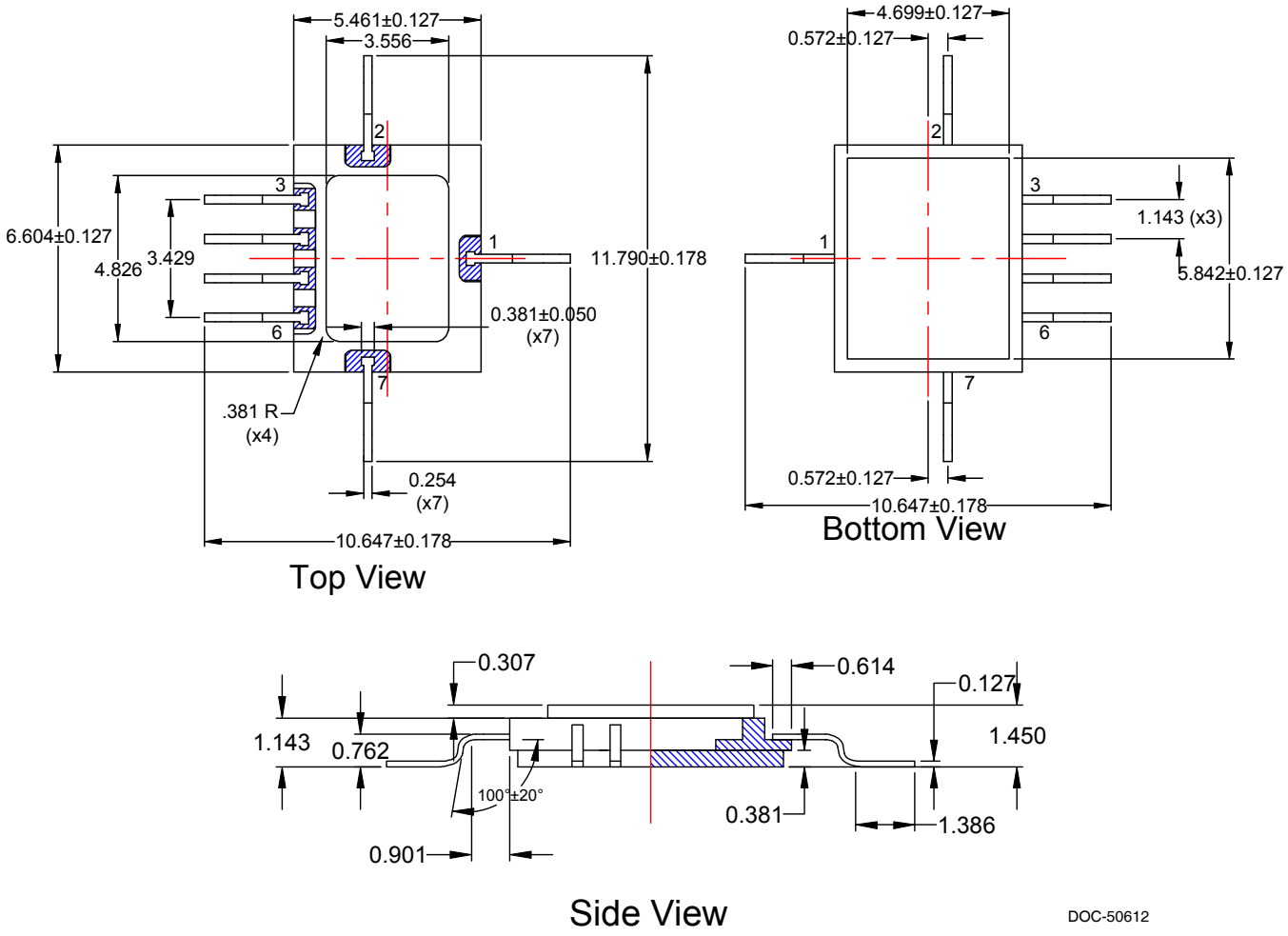
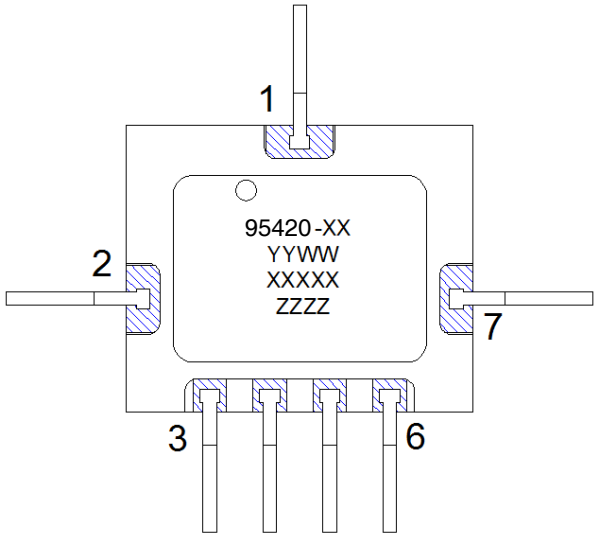


Figure 27. Top Marking Specification



O = Pin 1 indicator

95420-XX = Part number (XX will be specified by the PO and/or the assembly instructions)

YYWW = Date code, last two digits of the year and work week

XXXXX = Lot code (up to seven digits)

ZZZZ = Serial number (up to six digits)

PRT-24829

Table 7. Ordering Information

Order Code	Description	Package	Shipping Method
95420–01*	Engineering samples	7-lead CQFP	50 units / tray
95420–11	Production units	7-lead CQFP	50 units / tray
95420–00	PE95420 Evaluation kit	Evaluation board	1 / box

Note: * The PE95420-01 devices are engineering sample (ES) prototype units intended for use as initial evaluation units for customers of the PE95420-11 flight units. The PE95420-01 device provides the same functionality and footprint as the PE95420-11 space qualified device, and intended for engineering evaluation only. They are tested at +25 °C only and processed to a non-compliant flow (e.g. no burn-in, non-hermetic, etc). These units are non-hermetic and are not suitable for qualification, production, radiation testing or flight use.

Sales Contact and Information

For sales and contact information please visit www.psemi.com.